

IN THE ABSTRACT

Please delete the current Abstract and replace with the following new Abstract:

An electronic integrated circuit is fabricated by forming on a substrate, of which a part is composed of absorbing material, a portion made of a sacrificial material. The sacrificial material includes cobalt, nickel, titanium, tantalum, tungsten, molybdenum, gallium, indium, silver, gold, iron and/or chromium. A rigid portion is then formed in fixed contact with the substrate, on one side of the portion of sacrificial material opposite to the part of the substrate composed of absorbing material. The circuit is heated such that the sacrificial material is absorbed into the part of the substrate composed of absorbing material. A substantially empty volume is thus created in place of the portion of sacrificial material. The volume that is substantially empty can replace a dielectric material situated between the electrodes of a capacitor.

A replacement page containing the new Abstract in enclosed herewith.